



## ST13007FP

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- HIGH VOLTAGE CAPABILITY
- NPN TRANSISTOR
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125 °C
- LARGE RBSOA

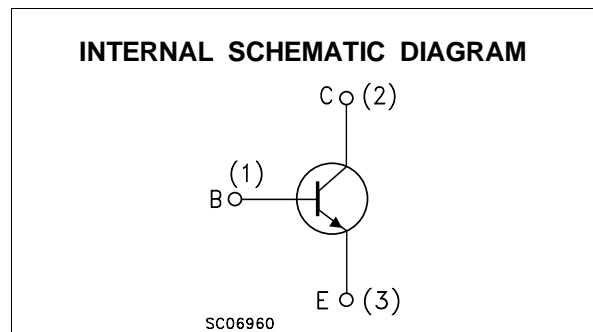
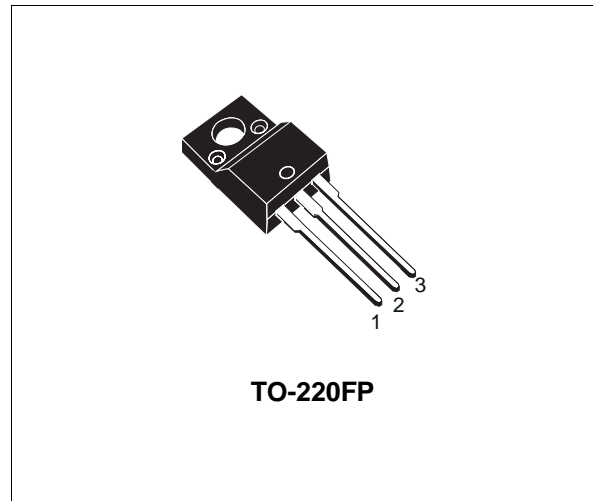
### APPLICATIONS

- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- SWITCH MODE POWER SUPPLIES

### DESCRIPTION

The device is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability.

They use a Cellular Emitter structure to enhance switching speeds.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CEV}$	Collector-Emitter Voltage ( $V_{BE} = -1.5V$ )	700	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	400	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	9	V
$I_C$	Collector Current	8	A
$I_{CM}$	Collector Peak Current	16	A
$I_B$	Base Current	4	A
$I_{BM}$	Base Peak Current	8	A
$P_{tot}$	Total Dissipation at $T_c \leq 25\text{ }^\circ\text{C}$	36	W
$T_{stg}$	Storage Temperature	-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$

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### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	3.47	°C/W
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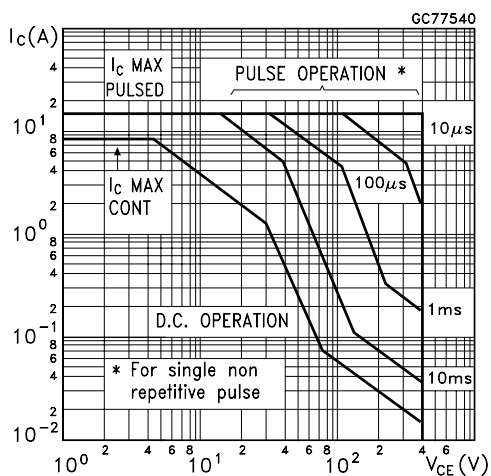
### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CEV</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V)	V <sub>CE</sub> = rated V <sub>CEV</sub> V <sub>CE</sub> = rated V <sub>CEV</sub> T <sub>c</sub> = 100 °C			1 5	mA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>c</sub> = 0)	V <sub>EB</sub> = 9 V			1	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage	I <sub>c</sub> = 10 mA	400			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>c</sub> = 2 A I <sub>B</sub> = 0.4 A I <sub>c</sub> = 5 A I <sub>B</sub> = 1 A I <sub>c</sub> = 8 A I <sub>B</sub> = 2 A I <sub>c</sub> = 5 A I <sub>B</sub> = 1 A T <sub>c</sub> = 100 °C			1 2 3 3	V V V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>c</sub> = 2 A I <sub>B</sub> = 0.4 A I <sub>c</sub> = 5 A I <sub>B</sub> = 1 A I <sub>c</sub> = 5 A I <sub>B</sub> = 1 A T <sub>c</sub> = 100 °C			1.2 1.6 1.5	V V V
h <sub>FE*</sub>	DC Current Gain	I <sub>c</sub> = 2 A V <sub>CE</sub> = 5 V Group A Group B I <sub>c</sub> = 5 A V <sub>CE</sub> = 5 V	15 26 5		28 40 30	
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>c</sub> = 5 A V <sub>CL</sub> = 250 V I <sub>B1</sub> = 1 A I <sub>B2</sub> = -2 A L = 200 μH		1.6 60	2.5 110	ms ns
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>c</sub> = 5 A V <sub>CL</sub> = 250 V I <sub>B1</sub> = 1 A I <sub>B2</sub> = -2 A L = 200 μH T <sub>c</sub> = 125 °C		2.3 110		μs ns

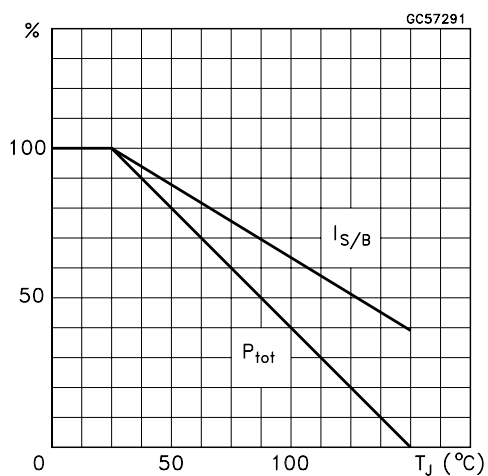
\* Pulsed: Pulse duration = 300 μs, duty cycle 2 %

Note : Product is pre-selected in DC current gain (GROUP A and GROUP B). STMicroelectronics reserves the right to ship either groups according to production availability. Please contact your nearest STMicroelectronics sales office for delivery details.

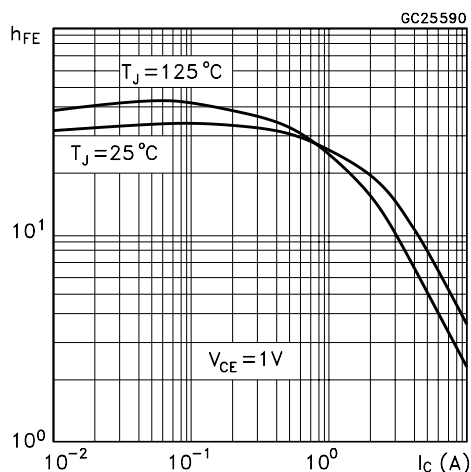
Safe Operating Areas



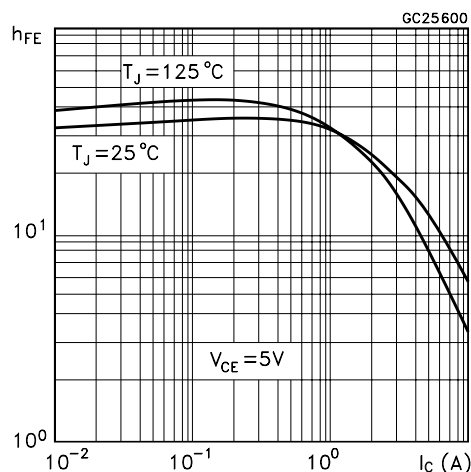
Derating Curve



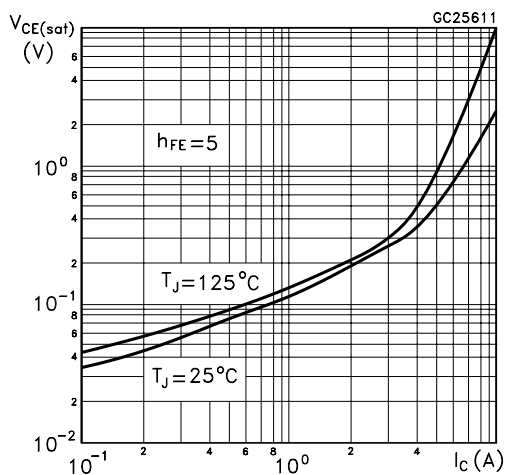
DC Current Gain



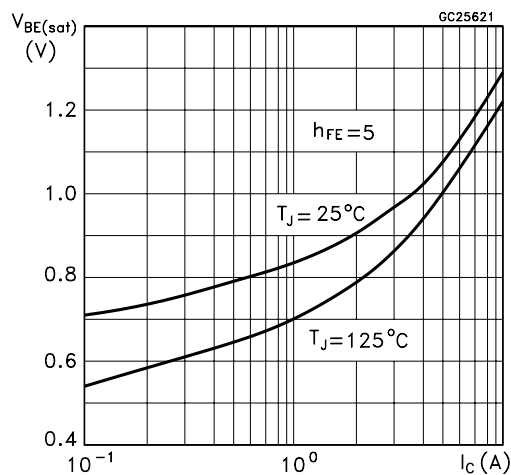
DC Current Gain



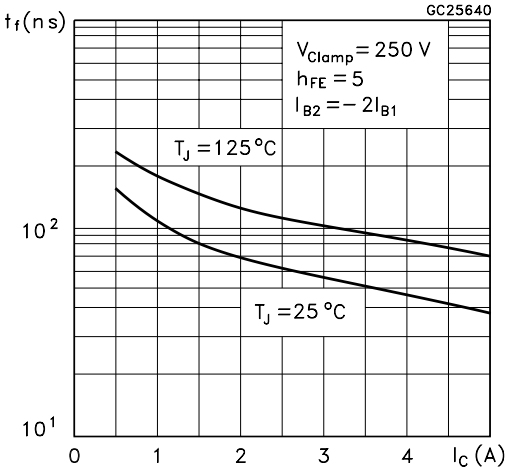
Collector Emitter Saturation Voltage



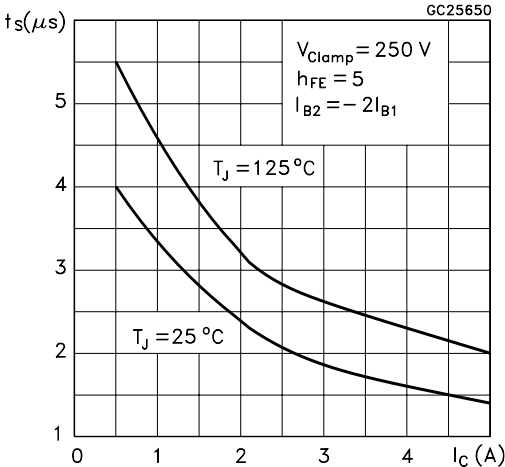
Base Emitter Saturation Voltage



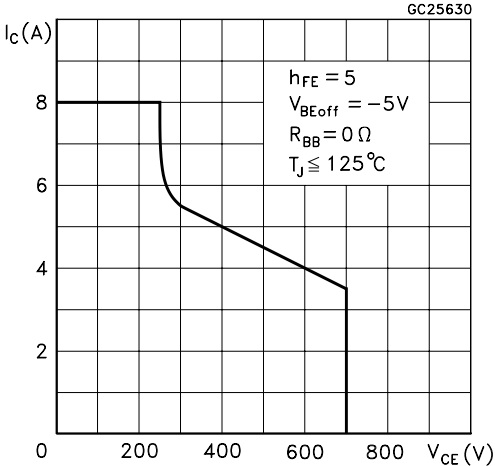
Inductive Fall Time



Inductive Storage Time

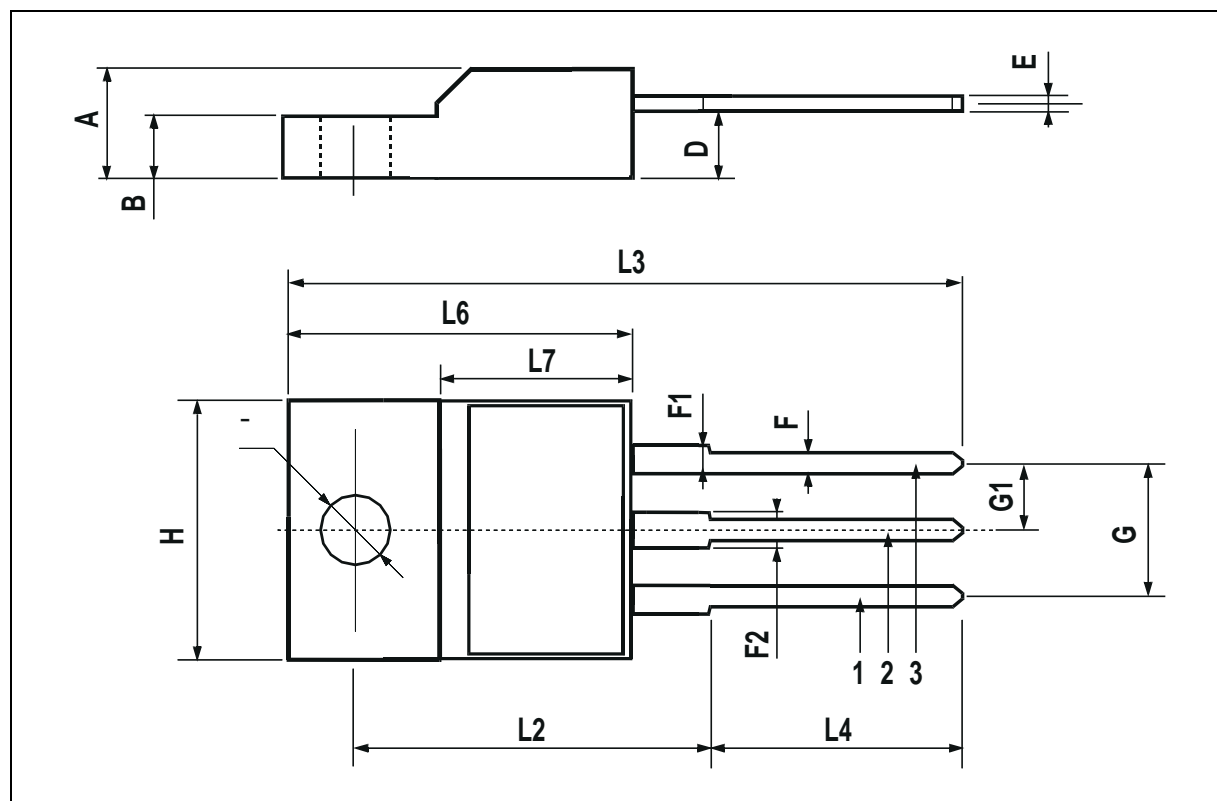


Reverse Biased SOA



## TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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